

MC78XX/MC78XXA

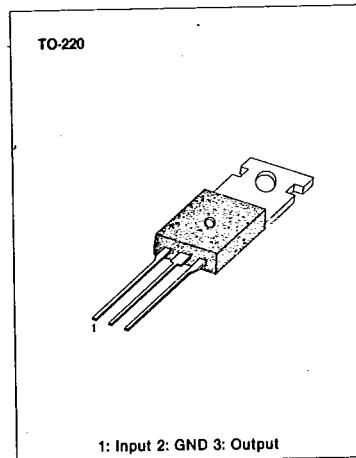
LINEAR INTEGRATED CIRCUIT

3-Terminal 1A Positive Voltage Regulators

The MC78XX/MC78XXA series of three-terminal positive regulators are available in TO-220 package and with several fixed output voltages, making it useful in a wide range of applications. These Regulators can provide local oncard regulation, eliminating the distribution problems associated with single point regulation. Each type employs internal current limiting, thermal shut-down and safe area protection, making it essentially indestructible. If adequate heat sinking is provided, they can deliver over 1A output current. Although designed primarily as fixed voltage regulators, these devices can be used with external components to obtain adjustable voltages and currents.

FEATURES

- Output Current up to 1.5A
- Output voltages of 5; 6; 8; 8.5; 9; 10; 11; 12; 15; 18; 24V
- Thermal Overload Protection
- Short Circuit Protection
- Output Transistor SOA Protection

BLOCK DIAGRAM

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ORDERING INFORMATION

Device	Package	Operating Temperature
MC78XXIT	TO-220	-40°C ~ +125°C
MC78XXCT	TO-220	0°C ~ +125°C
MC78XXACT	TO-220	

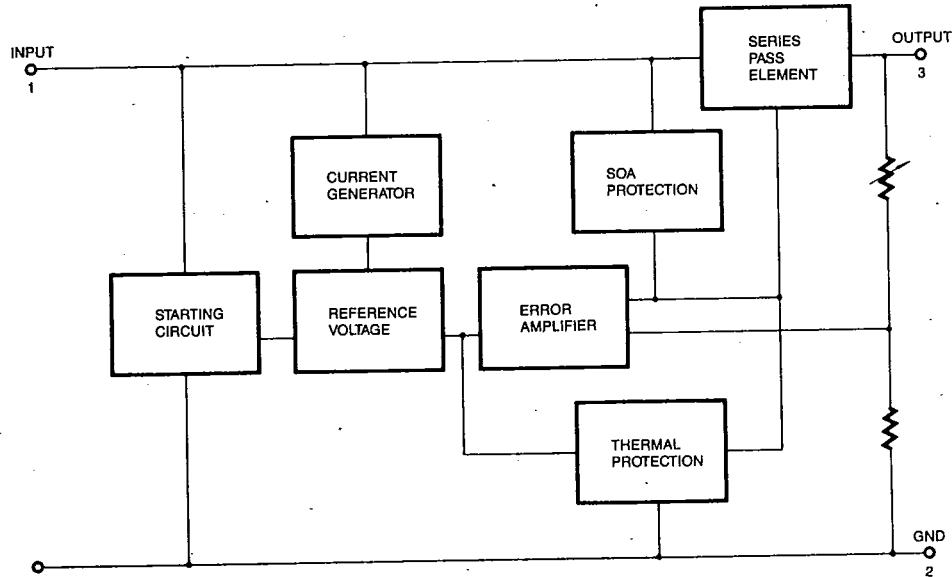


Fig. 1



SAMSUNG SEMICONDUCTOR

MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

SCHEMATIC DIAGRAM

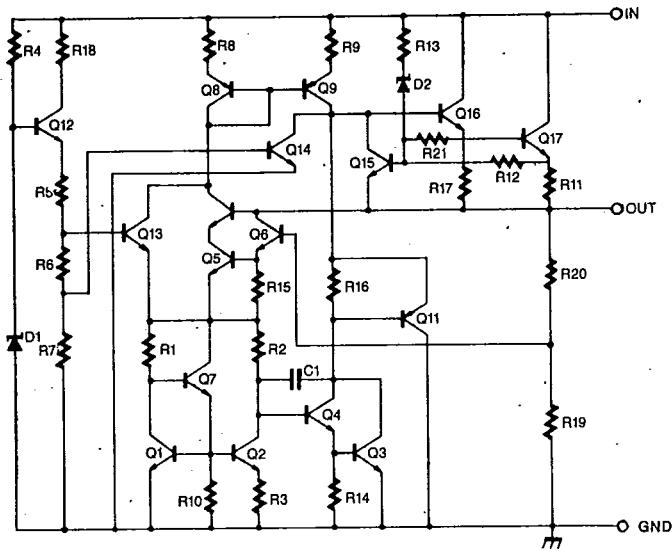


Fig. 2

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	Value	Unit
Input Voltage (for $V_o = 5V$ to $18V$) (for $V_o = 24V$)	V_i	35	V
Thermal Resistance Junction-Cases	Θ_{JC}	40	V
Thermal Resistance Junction-Air	Θ_{JA}	5	°C/W
Junction Operating Temperature MC78XXI MC78XXC/AC	T_{opr}	65	°C/W
Storage Temperature	T_{sig}	-40 ~ +150	°C
		0 ~ +150	°C
		-65 ~ +150	°C



SAMSUNG SEMICONDUCTOR

T-58-11-13

MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

ELECTRICAL CHARACTERISTICS MC7805

(Refer to test circuit, $T_{min} < T_j < T_{max}$, $I_o = 500mA$, $V_i = 10V$, $C_i = 0.33\mu F$, $C_o = 0.1\mu F$, unless otherwise specified)

Characteristic	Symbol	Test Conditions	MC7805I			MC7805C			Unit
			Min	Typ	Max	Min	Typ	Max	
Output Voltage	V_o	$T_j = 25^\circ C$	4.8	5.0	5.2	4.8	5.0	5.2	V
		$5.0mA \leq I_o \leq 1.0A, P_D \leq 15W$ $V_i = 7V$ to $20V$ $V_i = 8V$ to $20V$	4.75	5.0	5.25	4.75	5.0	5.25	
Line Regulation	ΔV_o	$T_j = 25^\circ C$	$V_i = 7V$ to $25V$	3.0	100	3.0	100	mV	
			$V_i = 8V$ to $12V$	1.0	50	1.0	50		
Load Regulation	ΔV_o	$T_j = 25^\circ C$	$I_o = 5.0mA$ to $1.5A$	15	100	15	100	mV	
			$I_o = 250mA$ to $750mA$	5	50	5	50		
Quiescent Current	I_d	$T_j = 25^\circ C$		4.2	8	4.2	8	mA	
Quiescent Current Change	ΔI_d	$I_o = 5mA$ to $1.0A$			0.5			0.5	mA
		$V_i = 7V$ to $25V$						1.3	
		$V_i = 8V$ to $25V$			1.3				
Output Voltage Drift	$\Delta V_o/\Delta T$	$I_o = 5mA$		-1.1			-1.1		mV/ $^\circ C$
Output Noise Voltage	V_N	$f = 10Hz$ to $100KHz, T_j = 25^\circ C$		40		40			μV
Ripple Rejection	RR	$f = 120Hz$ $V_i = 8$ to $18V$	62	78		62	78		dB
Dropout Voltage	V_o	$I_o = 1A, T_j = 25^\circ C$		2		2			V
Output Resistance	R_o	$f = 1KHz$		17		17			$m\Omega$
Short Circuit Current	I_{sc}	$V_i = 35V, T_j = 25^\circ C$		750		750			mA
Peak Current	I_{peak}	$T_j = 25^\circ C$		2.2		2.2			A

* $T_{min} < T_j < T_{max}$ MC78XXI: $T_{min} = -40^\circ C$, $T_{max} = 125^\circ C$ MC78XXC, $T_{min} = 0^\circ C$, $T_{max} = 125^\circ C$ * Load and line regulation are specified at constant junction temperature changes in V_o due to heating effects must be taken into account separately pulse testing with low duty is used.

SAMSUNG SEMICONDUCTOR

MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

ELECTRICAL CHARACTERISTICS MC7806

(Refer to test circuit, $T_{min} < T_j < T_{max}$, $I_o = 500mA$, $V_i = 11V$, $C_i = 0.33\mu F$, $C_o = 0.1\mu F$, unless otherwise specified)

Characteristic	Symbol	Test Conditions	MC7806I			MC7806C			Unit
			Min	Typ	Max	Min	Typ	Max	
Output Voltage	V_o	$T_j = 25^\circ C$	5.75	6.0	6.25	5.75	6.0	6.25	V
		$5.0mA \leq I_o \leq 1.0A$, $P_d \leq 15W$ $V_i = 8.0V$ to $21V$ $V_i = 9.0V$ to $21V$	5.7	6.0	6.3	5.7	6.0	6.3	
Line Regulation	ΔV_o	$T_j = 25^\circ C$	$V_i = 8V$ to $25V$	5	120	5	120	5	mV
			$V_i = 9V$ to $13V$	1.5	60	1.5	60	1.5	
Load Regulation	ΔV_o	$T_j = 25^\circ C$	$I_o = 5mA$ to $1.5A$	14	120	14	120	14	mV
			$I_o = 250mA$ to $750mA$	4	60	4	60	4	
Quiescent Current	I_d	$T_j = 25^\circ C$		4.3	8	4.3	8	4.3	mA
Quiescent Current Change	ΔI_d		$I_o = 5mA$ to $1A$		0.5			0.5	mA
			$V_i = 8V$ to $25V$					1.3	
			$V_i = 9V$ to $25V$		1.3				
Output Voltage Drift	$\Delta V_o/\Delta T$		$I_o = 5mA$	-0.8		-0.8		-0.8	$mV/^\circ C$
Output Noise Voltage	V_N	$f = 10Hz$ to $100KHz$ $T_j = 25^\circ C$		45		45		45	μV
Ripple Rejection	RR		$f = 120Hz$ $V_i = 9$ to $19V$	59	75	59	75	59	dB
Dropout Voltage	V_D		$I_o = 1A$, $T_j = 25^\circ C$	2		2		2	V
Output Resistance	R_o		$f = 1KHz$	19		19		19	$m\Omega$
Short Circuit Current	I_{sc}	$V_i = 35V$, $T_j = 25^\circ C$		550		550		550	mA
Peak Current	I_{peak}	$T_j = 25^\circ C$		2.2		2.2		2.2	A

* $T_{min} < T_j < T_{max}$ MC78XXI: $T_{min} = -40^\circ C$, $T_{max} = 125^\circ C$ MC78XXC, $T_{min} = 0^\circ C$, $T_{max} = 125^\circ C$ * Load and line regulation are specified at constant junction temperature changes in V_o due to heating effects must be taken into account separately pulse testing with low duty is used.

SAMSUNG SEMICONDUCTOR

T-58-11-13

MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

ELECTRICAL CHARACTERISTICS MC7808

(Refer to test circuit, $T_{min} < T_j < T_{max}$, $I_o = 500mA$, $V_i = 14V$, $C_i = 0.33\mu F$, $C_o = 0.1\mu F$, unless otherwise specified)

Characteristic	Symbol	Test Conditions	MC7808I			MC7808C			Unit
			Min	Typ	Max	Min	Typ	Max	
Output Voltage	V_o	$T_j = 25^\circ C$	7.7	8.0	8.3	7.7	8.0	8.3	V
		$5.0mA \leq I_o \leq 1.0A$, $P_D \leq 15W$ $V_i = 10.5V$ to $23V$ $V_i = 11.5V$ to $23V$	7.6	8.0	8.4	7.6	8.0	8.4	
Line Regulation	ΔV_o	$T_j = 25^\circ C$	$V_i = 10.5V$ to $25V$	6.0	160	6.0	160	6.0	mV
			$V_i = 11.5V$ to $17V$	2.0	80	2.0	80	2.0	
Load Regulation	ΔV_o	$T_j = 25^\circ C$	$I_o = 5.0mA$ to $1.5A$	12	160	12	160	12	mV
			$I_o = 250mA$ to $750mA$	4.0	80	4.0	80	4.0	
Quiescent Current	I_o	$T_j = 25^\circ C$		4.3	8	4.3	8	4.3	mA
Quiescent Current Change	ΔI_o	$I_o = 5mA$ to $1.0A$			0.5			0.5	mA
		$V_i = 10.5V$ to $25V$						1.0	
		$V_i = 11.5V$ to $25V$			1.0				
Output Voltage Drift	$\Delta V_o/\Delta T$	$I_o = 5mA$		-0.8		-0.8		-0.8	mV/ $^\circ C$
Output Noise Voltage	V_N	$f = 10Hz$ to $100KHz$ $T_j = 25^\circ C$		52		52		52	μV
Ripple Rejection	RR	$f = 120Hz$, $V_i = 11.5V$ to 21.5	56	72		56	72	56	dB
Dropout Voltage	V_o	$I_o = 1A$, $T_j = 25^\circ C$		2		2		2	V
Output Resistance	R_o	$f = 1KHz$		16		16		16	$m\Omega$
Short Circuit Current	I_{sc}	$V_i = 35V$, $T_j = 25^\circ C$		450		450		450	mA
Peak Current	I_{peak}	$T_j = 25^\circ C$		2.2		2.2		2.2	A

* $T_{min} < T_j < T_{max}$ MC78XXI: $T_{min} = -40^\circ C$, $T_{max} = 125^\circ C$ MC78XXC, $T_{min} = 0^\circ C$, $T_{max} = 125^\circ C$ * Load and line regulation are specified at constant junction temperature changes in V_o due to heating effects must be taken into account separately pulse testing with low duty is used.

SAMSUNG SEMICONDUCTOR

T-58-11-13

MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

ELECTRICAL CHARACTERISTICS MC7885

(Refer to test circuit $T_{min} < T_j < T_{max}$, $I_o = 500mA$, $V_i = 14.5V$, $C_i = 0.33\mu F$, $C_o = 0.1\mu F$, unless otherwise specified)

Characteristic	Symbol	Test Conditions	MC7885I			MC7885C			Unit
			Min	Typ	Max	Min	Typ	Max	
Output Voltage	V_o	$T_j = 25^\circ C$	8.15	8.5	8.85	8.15	8.5	8.85	V
		$I_o = 5mA$ to $1.0A$, $P_d \leq 15W$ $V_i = 11V$ to $23.5V$ $V_i = 12V$ to $23.5V$	8.1	8.5	8.9	8.1	8.5	8.9	
Line Regulation	ΔV_o	$T_j = 25^\circ C$	$V_i = 11V$ to $25V$	12	170	12	170	mV	
			$V_i = 11.5V$ to $18V$	5.0	85	5.0	85		
Load Regulation	ΔV_o	$T_j = 25^\circ C$	$I_o = 5mA$ to $1.5A$	45	170	45	170	mV	
			$I_o = 250mA$ to $750mA$	16	85	16	85		
Quiescent Current	I_d	$T_j = 25^\circ C$		4.3	8.0	4.3	8.0	mA	
Quiescent Current Change	ΔI_d	$I_o = 5mA$ to $1.0A$			0.5		0.5	mA	
		$V_i = 11V$ to $25V$					1.0		
		$V_i = 12V$ to $25V$			1.0				
Output Voltage Drift	$\Delta V_o/\Delta T$	$I_o = 5mA$		-1.0		-1.0		mV/ $^\circ C$	
Output Noise Voltage	V_N	$f = 10Hz$ to $100KHz$, $T_a = 25^\circ C$		55		55		μV	
Ripple Rejection	RR	$f = 120Hz$, $V_i = 12V$ to $22V$	56	72		56	72	dB	
Dropout Voltage	V_D	$I_o = 1.0A$, $T_j = 25^\circ C$		2.0		2.0		V	
Output Resistance	R_o	$f = 1KHz$		17		17		$m\Omega$	
Short Circuit Current	I_{sc}	$V_i = 35V$, $T_j = 25^\circ C$		450		450		mA	
Peak Current	I_{peak}	$T_j = 25^\circ C$		2.2		2.2		A	

* $T_{min} < T_j < T_{max}$ MC78XXI: $T_{min} = -40^\circ C$, $T_{max} = 125^\circ C$ MC78XXC: $T_{min} = 0^\circ C$, $T_{max} = 125^\circ C$ * Load and line regulation are specified at constant junction temperature changes in V_o due to heating effects must be taken into account separately pulse testing with low duty is used.

SAMSUNG SEMICONDUCTOR

T-58-11-13

MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

ELECTRICAL CHARACTERISTICS MC7809

(Refer to test circuit, $T_{min} < T_j < T_{max}$, $I_o = 500mA$, $V_i = 15V$, $C_i = 0.33\mu F$, $C_o = 0.1\mu F$, unless otherwise specified)

Characteristic	Symbol	Test Conditions	MC7809I			MC7809C			Unit
			Min	Typ	Max	Min	Typ	Max	
Output Voltage	V_o	$T_j = 25^\circ C$	8.65	9	9.35	8.65	9	9.35	V
		$5.0mA \leq I_o \leq 1.0A$, $P_D \leq 15W$ $V_i = 11.5V$ to $24V$ $V_i = 12.5V$ to $24V$	8.6	9	9.4	8.6	9	9.4	
Line Regulation	ΔV_o	$T_j = 25^\circ C$	$V_i = 11.5V$ to $25V$	6	180	6	180	mV	mV
			$V_i = 12V$ to $25V$	2	90	2	90		
Load Regulation	ΔV_o	$T_j = 25^\circ C$	$I_o = 5mA$ to $1.5A$	12	180	12	180	mV	mV
			$I_o = 250mA$ to $750mA$	4	80	4	90		
Quiescent Current	I_d	$T_j = 25^\circ C$		4.3	8	4.3	8.0	mA	
Quiescent Current Change	ΔI_d	$I_o = 5mA$ to $1.0A$			0.5		0.5		mA
		$V_i = 11.5V$ to $26V$					1.3		
		$V_i = 12.5V$ to $26V$			1.3				
Output Voltage Drift	$\Delta V_o/\Delta T$	$I_o = 5mA$		-1		-1		mV/ $^\circ C$	
Output Noise Voltage	V_N	$f = 10Hz$ to $100KHz$ $T_j = 25^\circ C$		58		58		μV	
Ripple Rejection	RR	$f = 120Hz$ $V_i = 13V$ to $23V$	56	71		56	71		dB
Dropout Voltage	V_D	$I_o = 1A$, $T_j = 25^\circ C$		2		2		V	
Output Resistance	R_o	$f = 1KHz$		17		17		$m\Omega$	
Short Circuit Current	I_{SC}	$V_i = 35V$, $T_j = 25^\circ C$		450		450		mA	
Peak Current	I_{peak}	$T_j = 25^\circ C$		2.2		2.2		A	

* $T_{min} < T_j < T_{max}$
 MC78XI: $T_{min} = -40^\circ C$, $T_{max} = 125^\circ C$
 MC78XC, $T_{min} = 0^\circ C$, $T_{max} = 125^\circ C$

* Load and line regulation are specified at constant junction temperature changes in V_o due to heating effects must be taken into account separately pulse testing with low duty is used.



SAMSUNG SEMICONDUCTOR

MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

ELECTRICAL CHARACTERISTICS MC7810

(Refer to test circuit, $T_{min} < T_j < T_{max}$, $I_o = 500mA$, $V_i = 16V$, $C_l = 0.33\mu F$, $C_o = 0.1\mu F$, unless otherwise specified)

Characteristic	Symbol	Test Conditions	MC7810I			MC7810C			Unit
			Min	Typ	Max	Min	Typ	Max	
Output Voltage	V_o	$T_j = 25^\circ C$	9.6	10	10.4	9.6	10	10.4	V
		$5.0mA \leq I_o \leq 1.0A$, $P_D \leq 15W$ $V_i = 12.5V$ to $25V$ $V_i = 13.5V$ to $25V$	9.5	10	10.5	9.5	10	10.5	
Line Regulation	ΔV_o	$T_j = 25^\circ C$	$V_i = 12.5V$ to $25V$	10	200		10	200	mV
			$V_i = 13V$ to $20V$	3	100		3	100	
Load Regulation	ΔV_o	$T_j = 25^\circ C$	$I_o = 5mA$ to $1.5A$	12	200		12	200	mV
			$I_o = 250mA$ to $750mA$	4	100		4	100	
Quiescent Current	I_d	$T_j = 25^\circ C$		4.3	8		4.3	8	mA
Quiescent Current Change	ΔI_d		$I_o = 5mA$ to $1.0A$		0.5			0.5	mA
			$V_i = 12.5V$ to $29V$					1.0	
			$V_i = 13.5V$ to $29V$		1.0				
Output Voltage Drift	$\Delta V_o/\Delta T$	$I_o = 5mA$		-1			-1		$mV/^\circ C$
Output Noise Voltage	V_N	$f = 10Hz$ to $100KHz$ $T_j = 25^\circ C$		58			58		μV
Ripple Rejection	RR	$f = 120Hz$ $V_i = 14V$ to $23V$	56	71		56	71		dB
Dropout Voltage	V_D	$I_o = 1A$, $T_j = 25^\circ C$		2			2		V
Output Resistance	R_o	$f = 1KHz$		17			17		$m\Omega$
Short Circuit Current	I_{sc}	$V_i = 35V$, $T_j = 25^\circ C$		420			420		mA
Peak Current	I_{peak}	$T_j = 25^\circ C$		2.2			2.2		A

• $T_{min} < T_j < T_{max}$ MC78XXI: $T_{min} = -40^\circ C$, $T_{max} = 125^\circ C$ MC78XXC, $T_{min} = 0^\circ C$, $T_{max} = 125^\circ C$ * Load and line regulation are specified at constant junction temperature changes in V_o due to heating effects must be taken into account separately pulse testing with low duty is used.

MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

ELECTRICAL CHARACTERISTICS MC7811

(Refer to test circuit, $T_{min} < T_j < T_{max}$, $I_o = 500\text{mA}$, $V_i = 18\text{V}$, $C_i = 0.33\mu\text{F}$, $C_o = 0.1\mu\text{F}$, unless otherwise specified)

Characteristic	Symbol	Test Conditions			MC7811I			MC7811C			Unit	
					Min	Typ	Max	Min	Typ	Max		
Output Voltage	V_o	$T_j = 25^\circ\text{C}$	10.6	11	11.4	10.6	11	11.4	V			
		5.0mA $\leq I_o \leq 1.0\text{A}$, $P_o \leq 15\text{W}$ $V_i = 13.5\text{V}$ to 26V $V_i = 14.5\text{V}$ to 26V	10.5	11	11.5	10.5	11	11.5				
Line Regulation	ΔV_o	$T_j = 25^\circ\text{C}$	$V_i = 13.5$ to 25V	10	220		10	220	mV			
			$V_i = 14$ to 21V	3.0	110		3.0	110				
Load Regulation	ΔV_o	$T_j = 25^\circ\text{C}$	$I_o = 5.0\text{mA}$ to 1.5A	12	220		12	220	mV			
			$I_o = 250\text{mA}$ to 750mA	4	110		4	110				
Quiescent Current	I_d	$T_j = 25^\circ\text{C}$			4.3	8		4.3	8	mA		
Quiescent Current Change	ΔI_d		$I_o = 5\text{mA}$ to 1A			0.5						
			$V_i = 13.5\text{V}$ to 29V						mA			
			$V_i = 14.5\text{V}$ to 29V			1.0						
Output Voltage Drift	$\Delta V_o/\Delta T$	$I_o = 5\text{mA}$			-1			-1		mV/ $^\circ\text{C}$		
Output Noise Voltage	V_N	$f = 10\text{Hz}$ to 100KHz $T_j = 25^\circ\text{C}$			70			70				
Ripple Rejection	RR	$f = 120\text{Hz}$ $V_i = 14\text{V}$ to 24V			55	71		55	71	dB		
Dropout Voltage	V_D	$I_o = 1\text{A}$, $T_j = 25^\circ\text{C}$			2			2				
Output Resistance	R_o	$f = 1\text{KHz}$			18			18		m Ω		
Short Circuit Current	I_{sc}	$V_i = 35\text{V}$, $T_j = 25^\circ\text{C}$			390			390				
Peak Current	I_{peak}	$T_j = 25^\circ\text{C}$			2.2			2.2		A		

* $T_{min} < T_j < T_{max}$ MC78XXI: $T_{min} = -40^\circ\text{C}$, $T_{max} = 125^\circ\text{C}$ MC78XXC, $T_{min} = 0^\circ\text{C}$, $T_{max} = 125^\circ\text{C}$ * Load and line regulation are specified at constant junction temperature changes in V_o due to heating effects must be taken into account separately pulse testing with low duty is used.

SAMSUNG SEMICONDUCTOR

MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

ELECTRICAL CHARACTERISTICS MC7812

(Refer to test circuit, $T_{min} < T_j < T_{max}$, $I_o = 500mA$, $V_i = 19V$, $C_l = 0.33\mu F$, $C_o = 0.1\mu F$, unless otherwise specified)

Characteristic	Symbol	Test Conditions	MC7812I			MC7812C			Unit
			Min	Typ	Max	Min	Typ	Max	
Output Voltage	V_o	$T_j = 25^\circ C$	11.5	12	12.5	11.5	12	12.5	V
		$5.0mA \leq I_o \leq 1.0A$, $P_D \leq 15W$ $V_{in} = 14.5V$ to $27V$ $V_i = 15.5V$ to $27V$	11.4	12	12.6	11.4	12	12.6	
Line Regulation	ΔV_o	$T_j = 25^\circ C$	$V_i = 14.5$ to $30V$	10	240	10	240	mV	
			$V_i = 16$ to $22V$	3.0	120	3.0	120		
Load Regulation	ΔV_o	$T_j = 25^\circ C$	$I_o = 5mA$ to $1.5A$	12	240	12	240	mV	
			$I_o = 250mA$ to $750mA$	4.0	120	4.0	120		
Quiescent Current	I_d	$T_j = 25^\circ C$		4.3	8	4.3	8	mA	
Quiescent Current Change	ΔI_d	$I_o = 5mA$ to $1.0A$			0.5		0.5	mA	
		$V_i = 14.5V$ to $30V$					1.0		
		$V_i = 15V$ to $30V$			1.0				
Output Voltage Drift	$\Delta V_o / \Delta T$	$I_o = 5mA$		-1		-1		$mV/^\circ C$	
Output Noise Voltage	V_N	$f = 10Hz$ to $100KHz$ $T_j = 25^\circ C$		75		75		μV	
Ripple Rejection	RR	$f = 120Hz$ $V_i = 15V$ to $25V$	55	71		55	71	dB	
Dropout Voltage	V_D	$I_o = 1A$, $T_j = 25^\circ C$		2		2		V	
Output Resistance	R_o	$f = 1KHz$		18		18		$m\Omega$	
Short Circuit Current	I_{sc}	$V_i = 35V$, $T_j = 25^\circ C$		350		350		mA	
Peak Current	I_{peak}	$T_j = 25^\circ C$		2.2		2.2		A	

* $T_{min} < T_j < T_{max}$ MC78XXI: $T_{min} = -40^\circ C$, $T_{max} = 125^\circ C$ MC78XXC, $T_{min} = 0^\circ C$, $T_{max} = 125^\circ C$ * Load and line regulation are specified at constant junction temperature changes in V_o due to heating effects must be taken into account separately pulse testing with low duty I_s is used.

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MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

ELECTRICAL CHARACTERISTICS MC7815

(Refer to test circuit, $T_{min} < T_j < T_{max}$, $I_o = 500mA$, $V_i = 23V$, $C_i = 0.33\mu F$, $C_o = 0.1\mu F$, unless otherwise specified)

Characteristic	Symbol	Test Conditions	MC7815I			MC7815C			Unit
			Min	Typ	Max	Min	Typ	Max	
Output Voltage	V_o	$T_j = 25^\circ C$	14.4	15	15.6	14.4	15	15.6	V
		$5.0mA \leq I_o \leq 1.0A$, $P_o \leq 15W$ $V_i = 17.5V$ to $30V$ $V_i = 18.5V$ to $30V$	14.25	15	15.75	14.25	15	15.75	
Line Regulation	ΔV_o	$T_j = 25^\circ C$	$V_i = 17.5$ to $30V$	11	300	11	300	mV	
			$V_i = 20$ to $26V$	3	150	3	150		
Load Regulation	ΔV_o	$T_j = 25^\circ C$	$I_o = 5.0mA$ to $1.5A$	12	300	12	300	mV	
			$I_o = 250mA$ to $750mA$	4	150	4	150		
Quiescent Current	I_d	$T_j = 25^\circ C$		4.4	8	4.4	8	mA	
Quiescent Current Change	ΔI_d	$I_o = 5mA$ to $1.0A$			0.5			mA	
		$V_i = 17.5V$ to $30V$							
		$V_i = 18.5V$ to $30V$			1.0				
Output Voltage Drift	$\Delta V_o/\Delta T$	$I_o = 5mA$		-1		-1		$mV/^\circ C$	
Output Noise Voltage	V_N	$f = 10Hz$ to $100KHz$ $T_j = 25^\circ C$		90		90		μV	
Ripple Rejection	RR	$f = 120Hz$ $V_i = 18.5V$ to $28.5V$	54	70		54	70	dB	
Dropout Voltage	V_D	$I_o = 1A$, $T_j = 25^\circ C$		2		2		V	
Output Resistance	R_o	$f = 1KHz$		19		19		$m\Omega$	
Short Circuit Current	I_{sc}	$V_i = 35V$, $T_j = 25^\circ C$		230		230		mA	
Peak Current	I_{peak}	$T_j = 25^\circ C$		2.2		2.2		A	

* $T_{min} < T_j < T_{max}$ MC78XXI: $T_{min} = -40^\circ C$, $T_{max} = 125^\circ C$ MC78XXC, $T_{min} = 0^\circ C$, $T_{max} = 125^\circ C$ * Load and line regulation are specified at constant junction temperature changes in V_o due to heating effects must be taken into account separately pulse testing with low duty is used.

MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

ELECTRICAL CHARACTERISTICS MC7818

(Refer to test circuit, $T_{min} < T_j < T_{max}$, $I_o = 500mA$, $V_i = 27V$, $C_i = 0.33\mu F$, $C_o = 0.1\mu F$, unless otherwise specified)

Characteristic	Symbol	Test Conditions	MC7818I			MC7818C			Unit
			Min	Typ	Max	Min	Typ	Max	
Output Voltage	V_o	$T_j = 25^\circ C$	17.3	18	18.7	17.3	18	18.7	V
		$5.0mA \leq I_o \leq 1.0A$, $P_D \leq 15W$ $V_i = 21V$ to $33V$ $V_i = 22V$ to $33V$	17.1	18	18.9	17.1	18	18.9	
Line Regulation	ΔV_o	$T_j = 25^\circ C$	$V_i = 21$ to $33V$	15	360	15	360	mV	mV
			$V_i = 24$ to $30V$	5	180	5	180		
Load Regulation	ΔV_o	$T_j = 25^\circ C$	$I_o = 5mA$ to $1.5A$	12	360	12	360	mV	mV
			$I_o = 250mA$ to $750mA$	4.0	180	4.0	180		
Quiescent Current	I_d	$T_j = 25^\circ C$		4.3	8	4.3	8	mA	
Quiescent Current Change	ΔI_d	$I_o = 5mA$ to $1A$			0.5			0.5	mA
		$V_i = 21V$ to $33V$						1	
		$V_i = 22V$ to $33V$			1				
Output Voltage Drift	$\Delta V_o/\Delta T$	$I_o = 5mA$		-1			-1	$mV/^\circ C$	
Output Noise Voltage	V_N	$f = 10Hz$ to $100KHz$ $T_j = 25^\circ C$		110			110	μV	
Ripple Rejection	RR	$f = 120Hz$ $V_i = 22V$ to $32V$	53	69		53	69		dB
Dropout Voltage	V_D	$I_o = 1A$, $T_j = 25^\circ C$		2			2	V	
Output Resistance	R_o	$f = 1KHz$		22			22	$m\Omega$	
Short Circuit Current	I_{sc}	$V_i = 35V$, $T_j = 25^\circ C$		200			200	mA	
Peak Current	I_{peak}	$T_j = 25^\circ C$		2.2			2.2	A	

- * $T_{min} < T_j < T_{max}$
MC78XXI: $T_{min} = -40^\circ C$, $T_{max} = 125^\circ C$
MC78XXC, $T_{min} = 0^\circ C$, $T_{max} = 125^\circ C$

- * Load and line regulation are specified at constant junction temperature changes in V_o due to heating effects must be taken into account separately pulse testing with low duty is used.



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MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

ELECTRICAL CHARACTERISTICS MC7824

(Refer to test circuit, $T_{min} < T_j < T_{max}$, $I_o = 500mA$, $V_i = 33V$, $C_i = 0.33\mu F$, $C_o = 0.1\mu F$, unless otherwise specified)

Characteristic	Symbol	Test Conditions	MC7824I			MC7824C			Unit
			Min	Typ	Max	Min	Typ	Max	
Output Voltage	V_o	$T_j = 25^\circ C$	23	24	25	23	24	25	V
		$5.0mA \leq I_o \leq 1.0A, P_D \leq 15W$ $V_i = 27V$ to $38V$ $V_i = 28V$ to $38V$	22.8	24	25.2	22.8	24	25.2	
Line Regulation	ΔV_o	$T_j = 25^\circ C$	$V_i = 27V$ to $38V$	18	480		18	480	mV
			$V_i = 30V$ to $36V$	6	240		6	240	
Load Regulation	ΔV_o	$T_j = 25^\circ C$	$I_o = 5mA$ to $1.5A$	12	480		12	480	mV
			$I_o = 250mA$ to $750mA$	4	240		4	240	
Quiescent Current	I_d	$T_j = 25^\circ C$		4.3	8		4.3	8	mA
Quiescent Current Change	ΔI_d	$I_o = 5mA$ to $1A$			0.5			0.5	mA
		$V_i = 27V$ to $38V$						1	
		$V_i = 28V$ to $38V$			1				
Output Voltage Drift	$\Delta V_o/\Delta T$	$I_o = 5mA$		-1.5			-1.5		mV/ $^\circ C$
Output Noise Voltage	V_N	$f = 10Hz$ to $100KHz$ $T_j = 25^\circ C$		170			170		μV
Ripple Rejection	RR	$f = 120Hz$ $V_i = 28V$ to $38V$	50	66		50	66		dB
Dropout Voltage	V_D	$I_o = 1A, T_j = 25^\circ C$		2			2		V
Output Resistance	R_o	$f = 1KHz$		28			28		$m\Omega$
Short Circuit Current	I_{sc}	$V_i = 35V, T_j = 25^\circ C$		150			150		mA
Peak Current	I_{peak}	$T_j = 25^\circ C$		2.2			2.2		A

* $T_{min} < T_j < T_{max}$ MC78XI: $T_{min} = -40^\circ C$, $T_{max} = 125^\circ C$ MC78XC, $T_{min} = 0^\circ C$, $T_{max} = 125^\circ C$ * Load and line regulation are specified at constant junction temperature changes in V_o due to heating effects must be taken into account separately pulse testing with low duty is used.

SAMSUNG SEMICONDUCTOR

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MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

ELECTRICAL CHARACTERISTICS MC7805AC

(Refer to the test circuits, $T_j=0$ to 125°C , $I_o=1\text{A}$, $V_i=10\text{V}$, $C_i=0.33\mu\text{F}$, $C_o=0.1\mu\text{F}$ unless otherwise specified)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Output Voltage	V_o	$T_j=25^\circ\text{C}$	4.9	5	5.1	V
		$I_o = 5\text{mA to } 1\text{A}, P_D \leq 15\text{W}$ $V_i = 7.5 \text{ to } 20\text{V}$	4.8	5	5.2	
*Line Regulation	ΔV_o	$V_i = 7.5 \text{ to } 25\text{V}$, $I_o = 500\text{mA}$		7	50	mV
		$V_i = 8 \text{ to } 12\text{V}$		10	50	
		$T_j=25^\circ\text{C}$	$V_i = 7.3 \text{ to } 25\text{V}$	7	50	
			$V_i = 8 \text{ to } 12\text{V}$	2	25	
*Load Regulation	ΔV_o	$T_j=25^\circ\text{C}$ $I_o = 5\text{mA to } 1.5\text{A}$		25	100	mV
		$I_o = 5\text{mA to } 1\text{A}$		25	100	
		$I_o = 250 \text{ to } 750\text{mA}$		8	50	
Quiescent Current	I_d	$T_j=25^\circ\text{C}$		4.3	6	mA
Quiescent Current Change	ΔI_d	$I_o = 5\text{mA to } 1\text{A}$			0.5	mA
		$V_i = 8 \text{ to } 25\text{V}, I_o = 500\text{mA}$			0.8	
		$V_i = 7.5 \text{ to } 20\text{V}, T_j = 25^\circ\text{C}$			0.8	
Output Voltage Drift	$\frac{\Delta V_o}{\Delta T}$	$I_o = 5\text{mA}$		-1.1		mV/°C
Output Noise Voltage	V_N	$f = 10\text{Hz to } 100\text{KHz}$ $T_a = 25^\circ\text{C}$		10		$\frac{\mu\text{V}}{V_o}$
Ripple Rejection	RR	$f = 120\text{Hz}, I_o = 500\text{mA}$ $V_i = 8 \text{ to } 18\text{V}$		68		dB
Dropout Voltage	V_D	$I_o = 1\text{A}, T_j = 25^\circ\text{C}$		2		V
Output Resistance	R_o	$f = 1\text{KHz}$		17		$\text{m}\Omega$
Short Circuit Current	I_{sc}	$V_i = 35\text{V}, T_a = 25^\circ\text{C}$		750		mA
Peak Current	I_{peak}	$T_j = 25^\circ\text{C}$		2.2		A

* Load and line regulation are specified at constant junction temperature. Changes in V_o due to heating effects must be taken into account separately. Pulse testing with low duty cycle is used.



SAMSUNG SEMICONDUCTOR

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MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

ELECTRICAL CHARACTERISTICS MC7806AC

(Refer to the test circuits, $T_j=0$ to 150°C , $I_o=1\text{A}$, $V_i=11\text{V}$, $C_i=0.33\mu\text{F}$, $C_o=0.1\mu\text{F}$ unless otherwise specified)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Output Voltage	V_o	$T_j=25^\circ\text{C}$	5.88	6	6.12	V
		$I_o = 5\text{mA to } 1\text{A}, P_D \leq 15\text{W}$ $V_i = 8.6 \text{ to } 21\text{V}$	5.76	6	6.24	
*Line Regulation	ΔV_o	$V_i = 8.6 \text{ to } 25\text{V}, I_o = 500\text{mA}$		9	60	mV
		$V_i = 9 \text{ to } 13\text{V}$		11	60	
		$T_j = 25^\circ\text{C} \quad V_i = 8.3 \text{ to } 21\text{V}$		9	60	
		$V_i = 9 \text{ to } 13\text{V}$		3	30	
*Load Regulation	ΔV_o	$T_j = 25^\circ\text{C}$ $I_o = 5\text{mA to } 1.5\text{A}$		43	100	mV
		$I_o = 5\text{mA to } 1\text{A}$		43	100	
		$I_o = 250 \text{ to } 750\text{mA}$		16	50	
Quiescent Current	I_d	$T_j = 25^\circ\text{C}$		4.3	6	mA
Quiescent Current Change	ΔI_d	$I_o = 5\text{mA to } 1\text{A}$			0.5	mA
		$V_i = 9 \text{ to } 25\text{V}, I_o = 500\text{mA}$			0.8	
		$V_i = 8.6 \text{ to } 21\text{V}, T_j = 25^\circ\text{C}$			0.8	
Output Voltage Drift	$\frac{\Delta V_o}{\Delta T}$	$I_o = 5\text{mA}$		-0.8		mV/ $^\circ\text{C}$
Output Noise Voltage	V_N	$f = 10\text{Hz to } 100\text{KHz}$ $T_a = 25^\circ\text{C}$		10		$\frac{\mu\text{V}}{V_o}$
Ripple Rejection	RR	$f = 120\text{Hz}, I_o = 500\text{mA}$ $V_i = 9 \text{ to } 19\text{V}$		65		dB
Dropout Voltage	V_d	$I_o = 1\text{A}, T_j = 25^\circ\text{C}$		2		V
Output Resistance	R_o	$f = 1\text{KHz}$		17		$\text{m}\Omega$
Short Circuit Current	I_{sc}	$V_i = 35\text{V}, T_a = 25^\circ\text{C}$		550		mA
Peak Current	I_{peak}	$T_j = 25^\circ\text{C}$		2.2		A

* Load and line regulation are specified at constant junction temperature. Changes in V_o due to heating effects must be taken into account separately. Pulse testing with low duty cycle is used.



SAMSUNG SEMICONDUCTOR

MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

ELECTRICAL CHARACTERISTICS MC7808AC

(Refer to the test circuits, $T_j=0$ to 150°C , $I_o=1\text{A}$, $V_i=14\text{V}$, $C_i=0.33\mu\text{F}$, $C_o=0.1\mu\text{F}$ unless otherwise specified)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Output Voltage	V_o	$T_j=25^\circ\text{C}$	7.84	8	8.16	V
		$I_o=5\text{mA}$ to 1A , $P_D \leq 15\text{W}$ $V_i=10.6$ to 23V	7.7	8	8.3	
*Line Regulation	ΔV_o	$V_i=10.6$ to 25V , $I_o=500\text{mA}$		12	80	mV
		$V_i=11$ to 17V		15	80	
		$T_j=25^\circ\text{C}$ $V_i=10.4$ to 23V $V_i=11$ to 17V		12	80	
*Load Regulation	ΔV_o	$T_j=25^\circ\text{C}$ $I_o=5\text{mA}$ to 1.5A		45	100	mV
		$I_o=5\text{mA}$ to 1A		45	100	
		$I_o=250$ to 750mA		16	50	
Quiescent Current	I_d	$T_j=25^\circ\text{C}$		4.3	6	mA
Quiescent Current Change	ΔI_d	$I_o=5\text{mA}$ to 1A			0.5	mA
		$V_i=11$ to 25V , $I_o=500\text{mA}$			0.8	
		$V_i=10.6$ to 23V , $T_j=25^\circ\text{C}$			0.8	
Output Voltage Drift	$\frac{\Delta V_o}{\Delta T}$	$I_o=5\text{mA}$		-0.8		mV/ $^\circ\text{C}$
Output Noise Voltage	V_N	$f=10\text{Hz}$ to 100KHz $T_a=25^\circ\text{C}$		10		$\frac{\mu\text{V}}{V_o}$
Ripple Rejection	RR	$f=120\text{Hz}$, $I_o=500\text{mA}$ $V_i=11.5$ to 21.5V		62		dB
Dropout Voltage	V_D	$I_o=1\text{A}$, $T_j=25^\circ\text{C}$		2		V
Output Resistance	R_o	$f=1\text{KHz}$		18		$\text{m}\Omega$
Short Circuit Current	I_{sc}	$V_i=35\text{V}$, $T_a=25^\circ\text{C}$		450		mA
Peak Current	I_{peak}	$T_j=25^\circ\text{C}$		2.2		A

* Load and line regulation are specified at constant junction temperature. Changes in V_o due to heating effects must be taken into account separately. Pulse testing with low duty cycle is used.



MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

ELECTRICAL CHARACTERISTICS MC7885AC

(Refer to the test circuits, $T_J = 0$ to 125°C , $I_o = 1\text{A}$, $V_i = 14\text{V}$, $C_i = 0.33\mu\text{F}$, $C_o = 0.1\mu\text{F}$ unless otherwise specified)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Output Voltage	V_o	$T_J = 25^\circ\text{C}$	8.33	8.5	8.67	V
		$I_o = 5\text{mA}$ to 1.0A , $P_D \leq 15\text{W}$ $V_i = 11.2\text{V}$ to 23.5V	8.15	8.5	8.85	
Line Regulation	ΔV_o	$V_i = 11.2\text{V}$ to 25V $I_o = 500\text{mA}$		12	85	mV
		$V_i = 11.5\text{V}$ to 18V		15	43	
		$T_J = 25^\circ\text{C}$ $V_i = 11\text{V}$ to 23.5V		12	85	
		$V_i = 11.5\text{V}$ to 18V		5.0	43	
Load Regulation	ΔV_o	$T_J = 25^\circ\text{C}$ $I_o = 5\text{mA}$ to 1.5A		45	100	mV
		$I_o = 5\text{mA}$ to 1.0A		45	100	
		$I_o = 250\text{mA}$ to 750mA		16	50	
Quiescent Current	I_d	$T_J = 25^\circ\text{C}$		4.3	6.0	mA
Quiescent Current Change	ΔI_d	$I_o = 5\text{mA}$ to 1.0A			0.5	mA
		$V_i = 11.5\text{V}$ to 25V , $T_J = 25^\circ\text{C}$			0.8	
		$V_i = 11.2\text{V}$ to 23.5V , $I_o = 500\text{mA}$			0.8	
Output Voltage Drift	$\Delta V_o/\Delta T$	$I_o = 5\text{mA}$		-1.0		mV/ $^\circ\text{C}$
Output Noise Voltage	V_N	$f = 10\text{Hz}$ to 100KHz , $T_a = 25^\circ\text{C}$		10		$\mu\text{V}/V_o$
Ripple Rejection	RR	$f = 120\text{Hz}$, $V_i = 12\text{V}$ to 22V $I_o = 500\text{mA}$		62		dB
Dropout Voltage	V_D	$I_o = 1.0\text{A}$, $T_J = 25^\circ\text{C}$		2.0		V
Output Resistance	R_o	$f = 1\text{KHz}$		17		m
Short Circuit Current	I_{short}	$V_i = 35\text{V}$, $T_a = 25^\circ\text{C}$		450		mA
Peak Current	I_{peak}	$T_J = 25^\circ\text{C}$		2.2		A

* Load and line regulation are specified at constant junction temperature. Changes in V_o due to heating effects must be taken into account separately. Pulse testing with low duty cycle is used.



SAMSUNG SEMICONDUCTOR

MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

ELECTRICAL CHARACTERISTICS MC7809AC

(Refer to the test circuits, $T_j = 0$ to 125°C , $I_o = 1\text{A}$, $V_i = 15\text{V}$, $C_i = 0.33\mu\text{F}$, $C_o = 0.1\mu\text{F}$ unless otherwise specified)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Output Voltage	V_o	$T_j = 25^\circ\text{C}$	8.82	9.0	9.18	V
		$I_o = 5\text{mA}$ to 1.0A , $P_D \leq 15\text{W}$ $V_i = 11.2\text{V}$ to 24V	8.65	9.0	9.35	
Line Regulation	ΔV_o	$V_i = 11.7\text{V}$ to 25V $I_o = 500\text{mA}$		12	90	mV
		$V_i = 12.5\text{V}$ to 19V		15	45	
		$T_j = 25^\circ\text{C}$ $V_i = 11.5\text{V}$ to 24V		12	90	
		$V_i = 12.5\text{V}$ to 19V		5.0	45	
Load Regulation	ΔV_o	$T_j = 25^\circ\text{C}$ $I_o = 5\text{mA}$ to 1.0A		46	100	mV
		$I_o = 5\text{mA}$ to 1.0A		46	100	
		$I_o = 250\text{mA}$ to 750mA		17	50	
Quiescent Current	I_d	$T_j = 25^\circ\text{C}$		4.3	6.0	mA
Quiescent Current Change	ΔI_d	$V_i = 11.7\text{V}$ to 24V , $T_j = 25^\circ\text{C}$			0.8	mA
		$V_i = 12\text{V}$ to 25V , $I_o = 500\text{mA}$			0.8	
		$I_o = 5\text{mA}$ to 1.0A			0.5	
Output Voltage Drift	$\Delta V_o/\Delta T$	$I_o = 5\text{mA}$		-1.0		mV/ $^\circ\text{C}$
Output Noise Voltage	V_N	$f = 10\text{Hz}$ to 100KHz , $T_a = 25^\circ\text{C}$		10		$\mu\text{V}/V_o$
Ripple Rejection	RR	$f = 120\text{Hz}$, $V_i = 12\text{V}$ to 22V $I_o = 500\text{mA}$		62		dB
Dropout Voltage	V_D	$I_o = 1.0\text{A}$, $T_j = 25^\circ\text{C}$		2.0		V
Output Resistance	R_o	$f = 1\text{KHz}$		17		m
Short Circuit Current	I_{short}	$V_i = 35\text{V}$, $T_j = 25^\circ\text{C}$		420		mA
Peak Current	I_{peak}	$T_j = 25^\circ\text{C}$		2.2		A

* Load and line regulation are specified at constant junction temperature. Changes in V_o due to heating effects must be taken into account separately. Pulse testing with low duty cycle is used.



SAMSUNG SEMICONDUCTOR

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MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

ELECTRICAL CHARACTERISTICS MC7811AC

(Refer to the test circuits, $T_j = 0$ to 125°C , $I_o = 1\text{A}$, $V_i = 18\text{V}$, $C_l = 0.33\mu\text{F}$, $C_o = 0.1\mu\text{F}$ unless otherwise specified)

Characteristic	Symbol	Test Conditions	Mln	Typ	Max	Unit
Output Voltage	V_o	$T_j = 25^\circ\text{C}$	10.8	11.0	11.2	V
		$I_o = 5\text{mA}$ to 1.0A , $P_D \leq 15\text{W}$ $V_i = 13.8\text{V}$ to 26V	10.6	11.0	11.4	
Line Regulation	ΔV_o	$V_i = 13.8\text{V}$ to 27V $I_o = 500\text{mA}$		13	110	mV
		$V_i = 15\text{V}$ to 21V		16	55	
		$T_j = 25^\circ\text{C}$ $V_i = 13.5\text{V}$ to 26V		13	110	
		$V_i = 15\text{V}$ to 21V		6.0	5.5	
Load Regulation	ΔV_o	$T_j = 25^\circ\text{C}$ $I_o = 5\text{mA}$ to 1.5A		46	100	mV
		$I_o = 5\text{mA}$ to 1.0A		46	100	
		$I_o = 250\text{mA}$ to 750mA		17	50	
Quiescent Current	I_d	$T_j = 25^\circ\text{C}$		4.4	6.0	mA
					6.0	
Quiescent Current Change	ΔI_d	$V_i = 13.8\text{V}$ to 26V , $T_j = 25^\circ\text{C}$			0.8	mA
		$V_i = 14\text{V}$ to 27V , $I_o = 500\text{mA}$			0.8	
		$I_o = 5\text{mA}$ to 1.0A			0.5	
Output Voltage Drift	$\Delta V_o/\Delta T$	$I_o = 5\text{mA}$		-1.0		$\text{mV}/^\circ\text{C}$
Output Noise Voltage	V_N	$f = 10\text{Hz}$ to 100KHz , $T_a = 25^\circ\text{C}$		10		$\mu\text{V}/V_o$
Ripple Rejection	RR	$f = 120\text{Hz}$, $V_i = 14\text{V}$ to 24V $I_o = 500\text{mA}$		61		dB
Dropout Voltage	V_D	$I_o = 1.0\text{A}$, $T_j = 25^\circ\text{C}$		2.0		V
Output Resistance	R_o	$f = 1\text{KHz}$		18		m
Short Circuit Current	I_{short}	$V_i = 35\text{V}$, $T_j = 25^\circ\text{C}$		390		mA
Peak Current	I_{peak}	$T_j = 25^\circ\text{C}$		2.2		A

* Load and line regulation are specified at constant junction temperature. Changes in V_o due to heating effects must be taken into account separately. Pulse testing with low duty cycle is used.



SAMSUNG SEMICONDUCTOR

T-58-11-13

MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

ELECTRICAL CHARACTERISTICS MC7812AC

(Refer to the test circuits, $T_J=0$ to 150°C , $I_o=1\text{A}$, $V_i=19\text{V}$, $C_i=0.33\mu\text{F}$, $C_o=0.1\mu\text{F}$ unless otherwise specified)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Output Voltage	V_o	$T_J=25^\circ\text{C}$	11.75	12	12.25	V
		$I_o=5\text{mA}$ to 1A , $P_D \leq 15\text{W}$ $V_i=14.8$ to 27V	11.5	12	12.5	
*Line Regulation	ΔV_o	$V_i=14.8$ to 30V , $I_o=500\text{mA}$		13	120	mV
		$V_i=16$ to 22V		16	120	
		$T_J=25^\circ\text{C}$ $V_i=14.5$ to 27V		13	120	
		$V_i=16$ to 22V		6	60	
*Load Regulation	ΔV_o	$T_J=25^\circ\text{C}$ $I_o=5\text{mA}$ to 1.5A		46	100	mV
		$I_o=5\text{mA}$ to 1A		46	100	
		$I_o=250$ to 750mA		17	50	
Quiescent Current	I_d	$T_J=25^\circ\text{C}$		4.4	6	mA
Quiescent Current Change	ΔI_d	$I_o=5\text{mA}$ to 1A			0.5	mA
		$V_i=15$ to 30V , $I_o=500\text{mA}$			0.8	
		$V_i=14.8$ to 27V , $T_J=25^\circ\text{C}$			0.8	
Output Voltage Drift	$\frac{\Delta V_o}{\Delta T}$	$I_o=5\text{mA}$		-1		mV/ $^\circ\text{C}$
Output Noise Voltage	V_N	$f=10\text{Hz}$ to 100KHz $T_a=25^\circ\text{C}$		10		$\frac{\mu\text{V}}{V_o}$
Ripple Rejection	RR	$f=120\text{Hz}$, $I_o=500\text{mA}$ $V_i=15$ to 25V		60		dB
Dropout Voltage	V_o	$I_o=1\text{A}$, $T_J=25^\circ\text{C}$		2		V
Output Resistance	R_o	$f=1\text{KHz}$		18		$\text{m}\Omega$
Short Circuit Current	I_{sc}	$V_i=35\text{V}$, $T_a=25^\circ\text{C}$		350		mA
Peak Current	I_{peak}	$T_J=25^\circ\text{C}$		2.2		A

* Load and line regulation are specified at constant junction temperature. Changes in V_o due to heating effects must be taken into account separately. Pulse testing with low duty cycle is used.



SAMSUNG SEMICONDUCTOR

T-58-11-13

MC78XXC/MC78XXAC SERIES LINEAR INTEGRATED CIRCUIT**ELECTRICAL CHARACTERISTICS MC7815AC**(Refer to the test circuits, $T_j=0$ to 150°C , $I_o=1\text{A}$, $V_i=23\text{V}$, $C_l=0.33\mu\text{F}$, $C_o=0.1\mu\text{F}$ unless otherwise specified)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Output Voltage	V_o	$T_j=25^\circ\text{C}$	14.7	15	15.3	V
		$I_o = 5\text{mA to } 1\text{A}, P_D \leq 15\text{W}$ $V_i = 17.7 \text{ to } 30\text{V}$	14.4	15	15.6	
*Line Regulation	ΔV_o	$V_i = 17.9 \text{ to } 30\text{V}, I_o = 500\text{mA}$		13	150	mV
		$V_i = 20 \text{ to } 26\text{V}$		16	150	
		$T_j=25^\circ\text{C} \quad V_i = 17.5 \text{ to } 30\text{V}$		13	150	
		$V_i = 20 \text{ to } 26\text{V}$		6	75	
*Load Regulation	ΔV_o	$T_j=25^\circ\text{C}$ $I_o = 5\text{mA to } 1.5\text{A}$		52	100	mV
		$I_o = 5\text{mA to } 1\text{A}$		52	100	
		$I_o = 250 \text{ to } 750\text{mA}$		20	50	
Quiescent Current	I_d	$T_j=25^\circ\text{C}$		4.4	6	mA
Quiescent Current Change	ΔI_d	$I_o = 5\text{mA to } 1\text{A}$			0.5	mA
		$V_i = 17.5 \text{ to } 30\text{V}, I_o = 500\text{mA}$			0.8	
		$V_i = 17.5 \text{ to } 30\text{V}, T_j = 25^\circ\text{C}$			0.8	
Output Voltage Drift	$\frac{\Delta V_o}{\Delta T}$	$I_o = 5\text{mA}$		-1		mV/ $^\circ\text{C}$
Output Noise Voltage	V_N	$f = 10\text{Hz to } 100\text{KHz}$ $T_a = 25^\circ\text{C}$		10		$\frac{\mu\text{V}}{V_o}$
Ripple Rejection	RR	$f = 120\text{Hz}, I_o = 500\text{mA}$ $V_i = 18.5 \text{ to } 28.5\text{V}$		58		dB
Dropout Voltage	V_D	$I_o = 1\text{A}, T_j = 25^\circ\text{C}$		2		V
Output Resistance	R_o	$f = 1\text{KHz}$		19		$\text{m}\Omega$
Short Circuit Current	I_{sc}	$V_i = 35\text{V}, T_a = 25^\circ\text{C}$		230		mA
Peak Current	I_{peak}	$T_j = 25^\circ\text{C}$		2.2		A

* Load and line regulation are specified at constant junction temperature. Changes in V_o due to heating effects must be taken into account separately. Pulse testing with low duty cycle is used.



SAMSUNG SEMICONDUCTOR

T-58-11-13

MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

ELECTRICAL CHARACTERISTICS MC7818AC

(Refer to the test circuits, $T_j=0$ to 150°C , $I_o=1\text{A}$, $V_i=27\text{V}$, $C_i=0.33\mu\text{F}$, $C_o=0.1\mu\text{F}$ unless otherwise specified)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Output Voltage	V_o	$T_j=25^\circ\text{C}$	17.64	18	18.36	V
		$I_o = 5\text{mA to } 1\text{A}, P_o \leq 15\text{W}$ $V_i = 21 \text{ to } 33\text{V}$	17.3	18	18.7	
*Line Regulation	ΔV_o	$V_i = 21 \text{ to } 33\text{V}, I_o = 500\text{mA}$		25	180	mV
		$V_i = 24 \text{ to } 30\text{V}$		28	180	
		$T_j=25^\circ\text{C} V_i = 20.6 \text{ to } 33\text{V}$		25	180	
*Load Regulation	ΔV_o	$V_i = 24 \text{ to } 30\text{V}$		10	90	mV
		$T_j=25^\circ\text{C}$ $I_o = 5\text{mA to } 1.5\text{A}$		55	100	
		$I_o = 5\text{mA to } 1\text{A}$		55	100	
Quiescent Current	I_d	$I_o = 250 \text{ to } 750\text{mA}$		22	50	mA
		$T_j=25^\circ\text{C}$		4.5	6	
		$I_o = 5\text{mA to } 1\text{A}$			0.5	
Quiescent Current Change	ΔI_d	$V_i = 21 \text{ to } 33\text{V}, I_o = 500\text{mA}$			0.8	mA
		$V_i = 21 \text{ to } 33\text{V}, T_j = 25^\circ\text{C}$			0.8	
		$I_o = 5\text{mA}$		-1		
Output Voltage Drift	$\frac{\Delta V_o}{\Delta T}$					mV/ $^\circ\text{C}$
Output Noise Voltage	V_N	$f = 10\text{Hz to } 100\text{KHz}$ $T_a = 25^\circ\text{C}$		10		$\frac{\mu\text{V}}{V_o}$
Ripple Rejection	RR	$f = 120\text{Hz}, I_o = 500\text{mA}$ $V_i = 22 \text{ to } 32\text{V}$		57		dB
Dropout Voltage	V_D	$I_o = 1\text{A}, T_j = 25^\circ\text{C}$		2		V
Output Resistance	R_o	$f = 1\text{KHz}$		19		$\text{m}\Omega$
Short Circuit Current	I_{sc}	$V_i = 35\text{V}, T_a = 25^\circ\text{C}$		200		mA
Peak Current	I_{peak}	$T_j = 25^\circ\text{C}$		2.2		A

* Load and line regulation are specified at constant junction temperature. Changes in V_o due to heating effects must be taken into account separately. Pulse testing with low duty cycle is used.



SAMSUNG SEMICONDUCTOR

T-58-11-13

MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

ELECTRICAL CHARACTERISTICS MC7824AC

(Refer to the test circuits, $T_j=0$ to 150°C , $I_o=1\text{A}$, $V_i=33\text{V}$, $C_l=0.33\mu\text{F}$, $C_o=0.1\mu\text{F}$ unless otherwise specified)

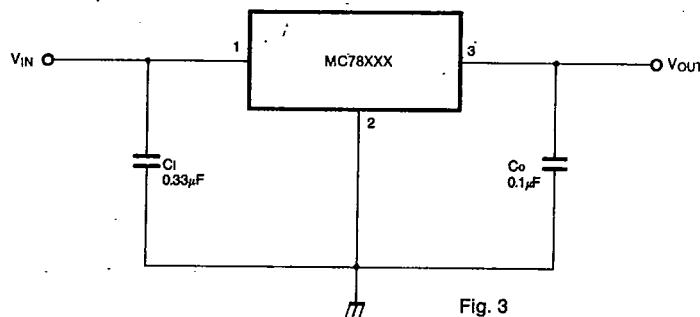
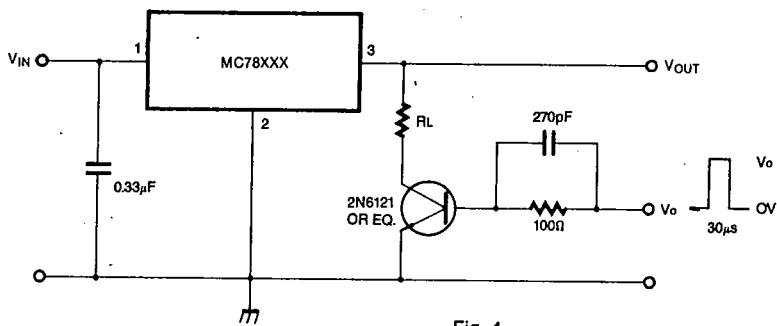
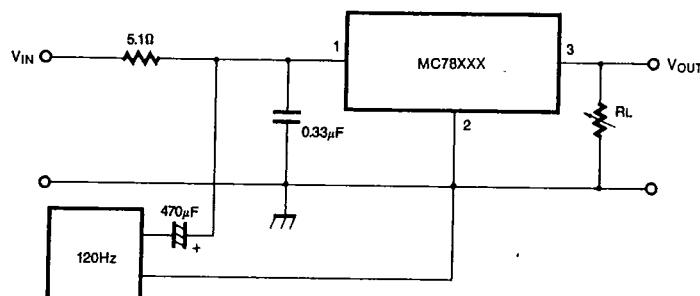
Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Output Voltage	V_o	$T_j=25^\circ\text{C}$	23.5	24	24.5	V
		$I_o = 5\text{mA to } 1\text{A}, P_o \leq 15\text{W}$ $V_i = 27.3 \text{ to } 38\text{V}$	23	24	25	
*Line Regulation	ΔV_o	$V_i = 27 \text{ to } 38\text{V}, I_o = 500\text{mA}$		31	240	mV
		$V_i = 30 \text{ to } 36\text{V}$		35	240	
		$T_j=25^\circ\text{C} V_i=26.7 \text{ to } 38\text{V}$		31	240	
		$V_i = 30 \text{ to } 36\text{V}$		14	120	
*Load Regulation	ΔV_o	$T_j=25^\circ\text{C}$ $I_o = 5\text{mA to } 1.5\text{A}$		60	100	mV
		$I_o = 5\text{mA to } 1\text{A}$		60	100	
		$I_o = 250 \text{ to } 750\text{mA}$		25	50	
Quiescent Current	I_d	$T_j=25^\circ\text{C}$		4.6	6	mA
Quiescent Current Change	ΔI_d	$I_o = 5\text{mA to } 1\text{A}$			0.5	mA
		$V_i = 27.3 \text{ to } 38\text{V}, I_o = 500\text{mA}$			0.8	
		$V_i = 27.3 \text{ to } 38\text{V}, T_j = 25^\circ\text{C}$			0.8	
Output Voltage Drift	$\frac{\Delta V_o}{\Delta T}$	$I_o = 1\text{mA}$		-1.5		mV/°C
Output Noise Voltage	V_N	$f = 10\text{Hz to } 100\text{KHz}$ $T_a = 25^\circ\text{C}$		10		$\frac{\mu\text{V}}{V_o}$
Ripple Rejection	RR	$f = 120\text{Hz}, I_o = 500\text{mA}$ $V_i = 28 \text{ to } 38\text{V}$		54		dB
Dropout Voltage	V_D	$I_o = 1\text{A}, T_j = 25^\circ\text{C}$		2		V
Output Resistance	R_o	$f = 1\text{KHz}$		20		$\text{m}\Omega$
Short Circuit Current	I_{sc}	$V_i = 35\text{V}, T_a = 25^\circ\text{C}$		150		mA
Peak Current	I_{peak}	$T_j = 25^\circ\text{C}$		2.2		A

* Load and line regulation are specified at constant junction temperature. Changes in V_o due to heating effects must be taken into account separately. Pulse testing with low duty cycle is used.



SAMSUNG SEMICONDUCTOR

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MC78XX/MC78XXA**LINEAR INTEGRATED CIRCUIT****TEST CIRCUIT****DC parameters****Load regulation****Ripple rejection****SAMSUNG SEMICONDUCTOR**

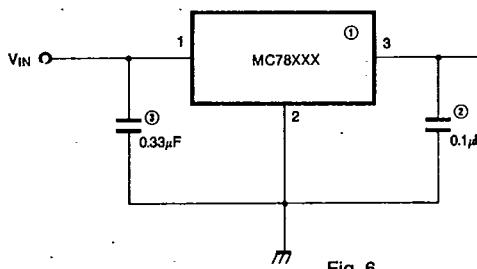
T-58-11-13

MC78XX/MC78XXA

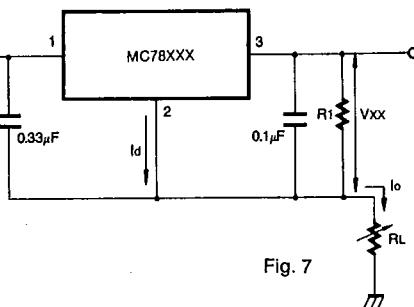
LINEAR INTEGRATED CIRCUIT

APPLICATION CIRCUIT

Fixed output regulator



Constant current regulator

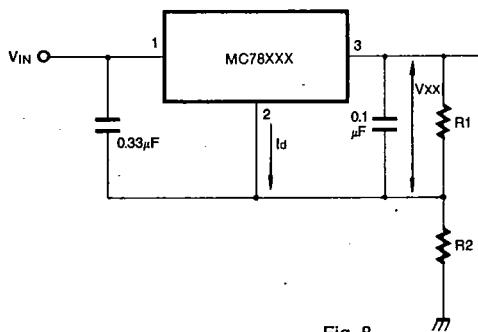


Notes:

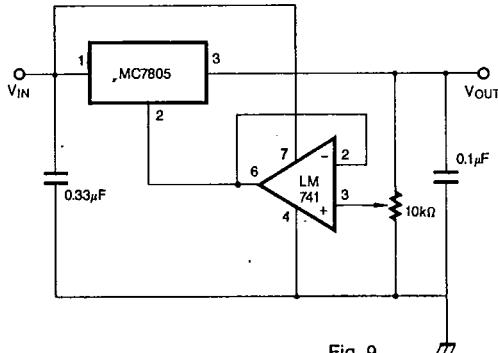
- (1) To specify an output voltage, substitute voltage value for "XX."
- (2) Although no output capacitor is needed for stability, it does improve transient response.
- (3) Required if regulator is located an appreciable distance from power supply filter.

$$I_o = \frac{V_{xx}}{R_1} + I_d$$

Circuit for increasing output voltage



Adjustable output regulator (7 to 30V)



$$I_{R1} \geq 5I_d$$

$$V_O = V_{xx} (1 + R_2/R_1) + I_d R_2$$



SAMSUNG SEMICONDUCTOR

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MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

APPLICATION CIRCUIT (continued)

0.5 to 10V regulator

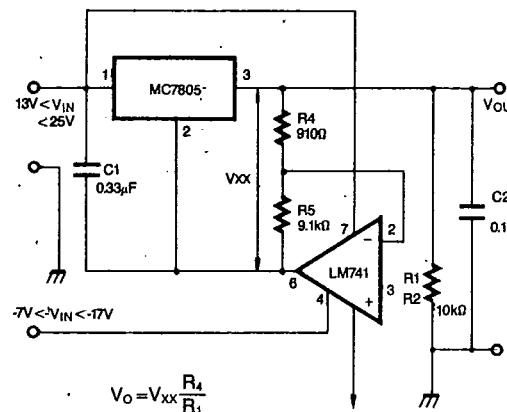


Fig. 10

High current voltage regulator

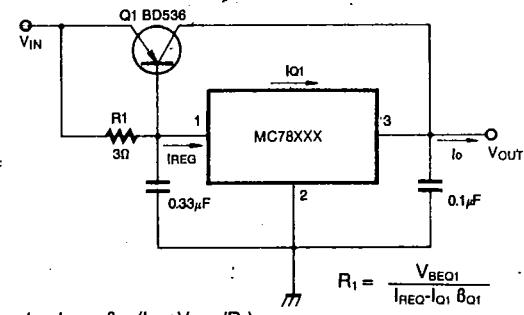


Fig. 11

High output current with short circuit protection

Tracking voltage regulator

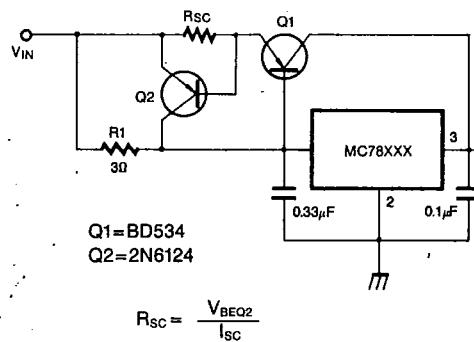


Fig. 12

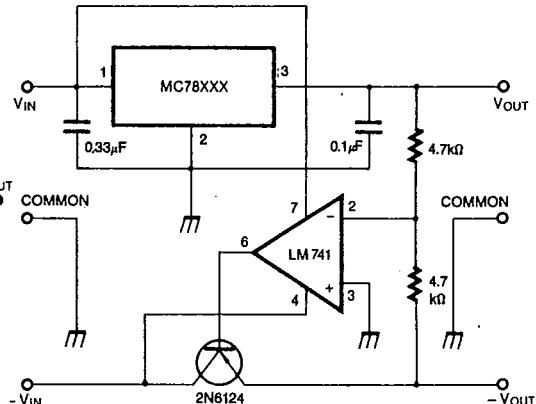


Fig. 13



SAMSUNG SEMICONDUCTOR

T-58-11-13

MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

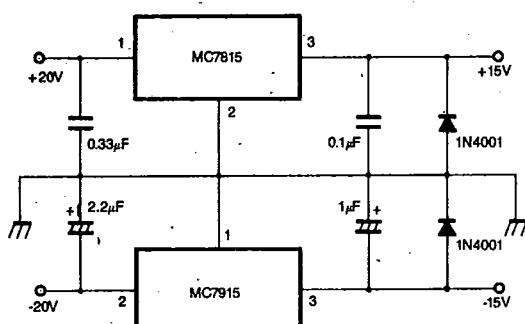
Split power supply ($\pm 15V - 1A$)

Fig. 14

Negative output voltage circuit

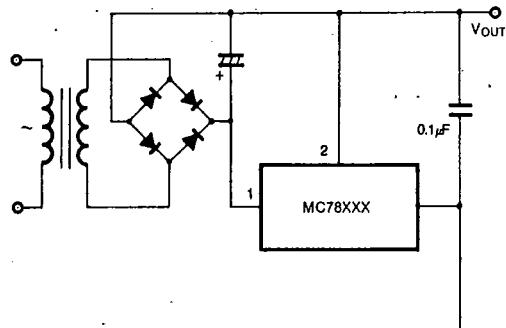


Fig. 15

Switching regulator

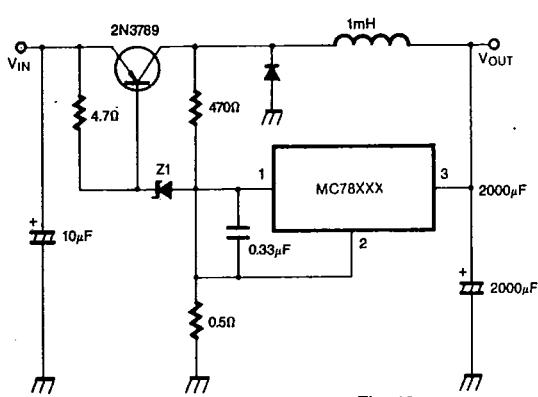
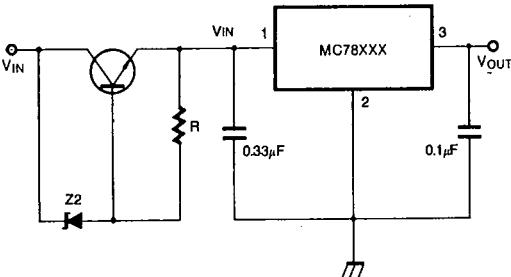


Fig. 16

High input voltage circuit



$$V_{IN} = V_i - (V_z + V_{BE})$$

Fig. 17



SAMSUNG SEMICONDUCTOR

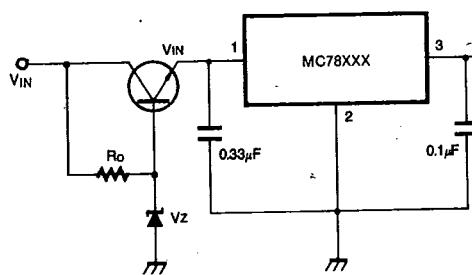
T-58-11-13

MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

APPLICATION CIRCUIT (continued)

High input voltage circuit



High output voltage regulator

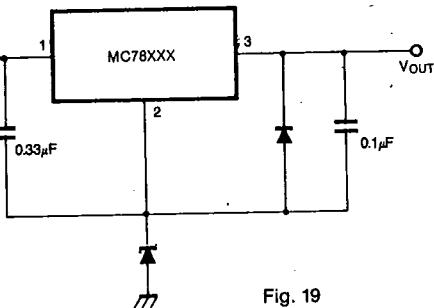
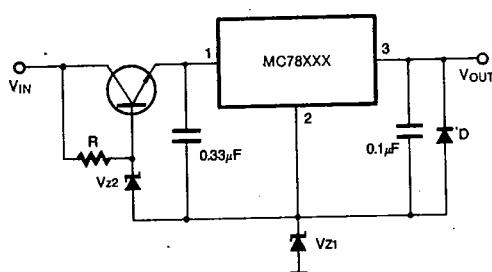


Fig. 18

Fig. 19

$$V_{IN} = V_Z - V_{BE}$$

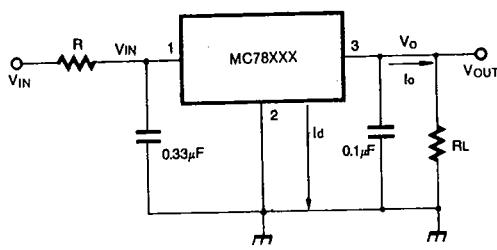
High input and output voltage



$$V_O = V_{XX} + V_{Z1}$$

Fig. 20

Reducing power dissipation with dropping resistor



$$R = \frac{V_{I(\min)} V_{XX} V_{DROP(max)}}{I_{O(max)} + I_{O(min)}}$$

Fig. 21



SAMSUNG SEMICONDUCTOR

MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

APPLICATION CIRCUIT (continued)

Remote shutdown

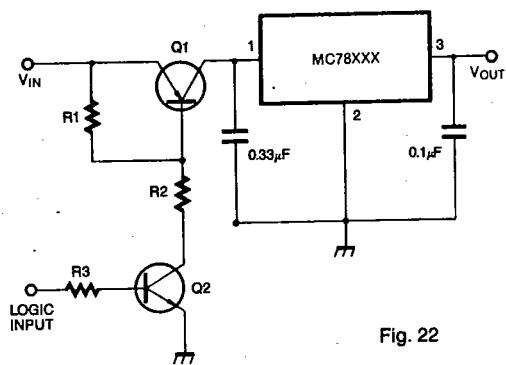


Fig. 22

Power AM modulator
(unity voltage gain, $I_o \leq 1A$)

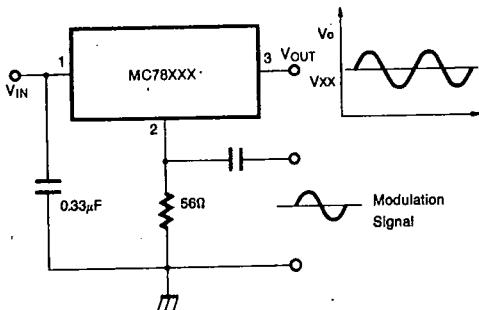


Fig. 23

Note: The circuit performs well up to 100 KHz.

4

Adjustable output voltage with temperature compensation

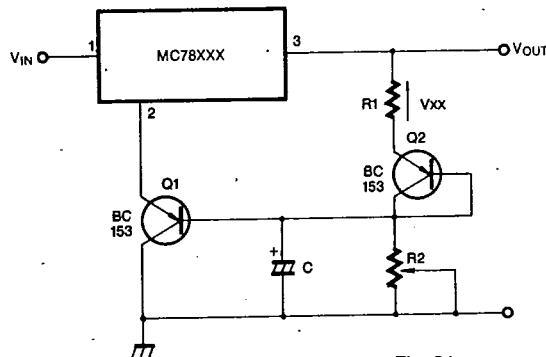


Fig. 24

Note: Q2 is connected as a diode in order to compensate the variation of the Q1 V_{BE} with the temperature. C allows a slow rise-time of the V_O

$$V_O = V_{xx} \left(1 + \frac{R_2}{R_1}\right) + V_{BE}$$

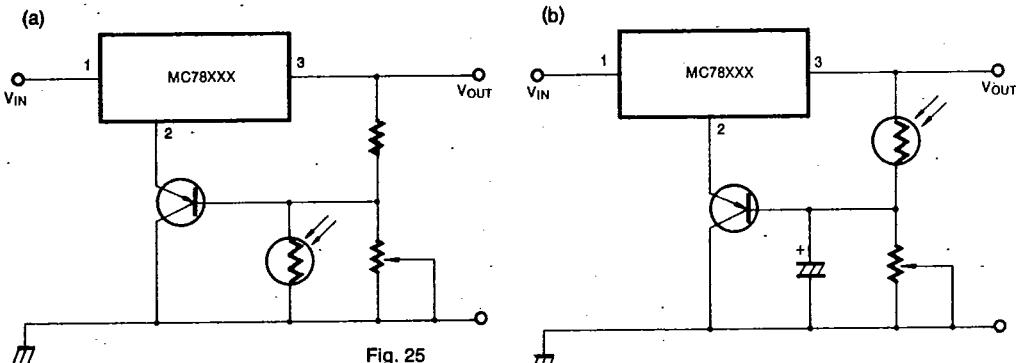


SAMSUNG SEMICONDUCTOR

MC78XX/MC78XXA

LINEAR INTEGRATED CIRCUIT

Light controllers ($V_o \text{ min} = V_{xx} + V_{BE}$)



Protection against input short-circuit with high capacitance loads

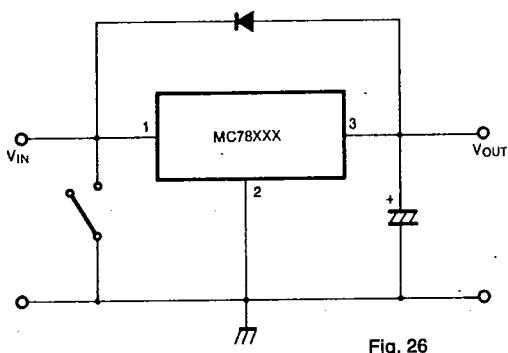


Fig. 26

Applications with high capacitance loads and an output voltage greater than 6 volts need an external diode (see fig. 26) to protect the device against input short circuit. In this case the input voltage falls rapidly while the output voltage decreases slowly. The capacitance discharges by means of the Base-Emitter junction of the series pass transistor in the regulator. If the energy is sufficiently high, the transistor may be destroyed. The external diode bypasses the current from the IC to ground.



SAMSUNG SEMICONDUCTOR